

# Design and Implementation of Fully-Integrated Inductive DC-DC Converters in Standard CMOS

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Mike Wens • Michiel Steyaert

# Design and Implementation of Fully-Integrated Inductive DC-DC Converters in Standard CMOS



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ISBN 978-94-007-1435-9  
DOI 10.1007/978-94-007-1436-6  
Springer Dordrecht Heidelberg London New York

e-ISBN 978-94-007-1436-6

Library of Congress Control Number: 2011928697

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*Cover design:* VTeX UAB, Lithuania

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*To my wife Larissa and our daughter Anna*

# Preface

Technological progress in the semiconductor industry has led to a revolution towards new advanced, miniaturized, intelligent, battery-operated and wireless electronic applications. The base of this still ongoing revolution, commonly known as Moore's law, is the ability to manufacture ever decreasing transistor sizes onto a CMOS chip. In other words, the transistor density increases, leading to larger quantity of transistors which can be integrated onto the same single chip die area. As a consequence, more functionality can be integrated onto a single chip die, leading to Systems-on-Chip (SoC) and reducing the total system cost. Indeed, the cost of electronic applications depends in an inverse-proportional fashion on the degree of on-chip integration, which is the main drive for CMOS scaling.

A SoC requires both analog and digital circuitry to be combined in order for it to be able to interact with the analog world. Nevertheless, it is usually processed in a native digital CMOS technology. These CMOS technologies are optimized for the integration of large-scale digital circuits, using very small transistors and low power supply voltages to reduce the power consumption. Beside for the purpose of decreasing the (dynamic) power consumption, the power supply voltage of deep-submicron CMOS technologies is also limited due to the physically very thin gate-oxide of the transistors. This thin gate-oxide, of which the thickness may merely be a few atom layers, would otherwise suffer electrical breakdown. However, the analog circuitry generally needs higher power supply voltages, compared to the digital circuitry. For instance, a power amplifier needs a higher supply voltage to deliver sufficient power into the communication medium. Also, analog signal processing blocks require a higher supply voltage to achieve the desired Signal-to-Noise-Ratio (SNR).

Due to the trend towards electronic applications of portable and wireless nature, (rechargeable) batteries are mandatory to provide the required energy. Although also prone to innovation and improvement, the battery voltage does not scale with the CMOS technology power supply voltages. Obviously, this is due to their physical and chemical constraints. Moreover, their energy density remains limited, limiting the available power and/or the autonomy of the application. Therefore, it is clear that power-management on a SoC-scale is mandatory for ensuring the ongoing feasibility of these applications.

Matching the battery voltage to the required power supply voltage(s) of the SoC can essentially be done in two ways. The first method, which can only be used when the battery voltage is higher than the required power supply voltage(s), is the use of linear voltage converters. This method is very often applied in current state-of-the-art applications, due to the simplicity to integrate it onto the SoC and its low associated cost. However, the excess energy from the battery voltage is dissipated in the form of waste heat, negatively influencing the autonomy and/or physical size of the application. The second method, putting no constraints to the battery voltage, is the use of switched-mode Direct-Current to Direct-Current (DC-DC) voltage converters. These converters are able to increase or decrease the battery voltage in a power-efficient fashion, leading to potentially higher battery autonomies. As a drawback, these switched-mode DC-DC converters are more complex and difficult to integrate onto the SoC, which is why they still require off-chip electronic components, such as inductors and capacitors.

The focus of the presented work is to integrate the switched-mode DC-DC converters onto the SoC, thus reducing both the number of external components and the Printed Circuit Board (PCB) footprint area. However, the poor electrical properties (low Q-factors) of on-chip inductors and capacitors and their low associated values (nH, nF) poses many difficulties, potentially compromising the power conversion efficiency advantage. Combining both the concepts of monolithic SoC integration and achieving a maximal (overall) power conversion efficiency, is the key to success. Moreover, to minimize the costs, the power density of the fully-integrated DC-DC converter is to be maximized.

To achieve these goals a firm theoretical base on the matter of DC-DC conversion is provided, leading to the optimal inductive DC-DC converter topology choices. An extensive mathematical steady-state model is deduced, in order to accurately predict both the trade-offs and performance limits of the inductive DC-DC converters. A further increase the performance of DC-DC converters is achieved through the design of novel control techniques, which are particularly optimized for high-frequency monolithic inductive DC-DC converters. Finally, the theory and simulations are verified and validated through the realization of seven monolithic inductive CMOS DC-DC converters. As such, the highest power density and Efficiency Enhancement Factor (EEF) over a linear voltage converter are obtained, in addition to the feasibility proofing of various novel concepts.

The authors also wish to express their gratitude to all persons who have contributed to this scientific research and the resulting book. We would like to thank Prof. R. Puers and Prof. W. Dehaene for their useful comments. In addition we would like to thank the colleagues of the ESAT-MICAS laboratories of K.U. Leuven for both the direct and indirect contributions to the presented work. Finally, we thank our families for their unconditional support and patience.

Leuven

Mike Wens  
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# Abbreviations and Symbols

## *Abbreviations*

AC	Alternating-Current
AC-AC	Alternating-Current to Alternating-Current
AC-DC	Alternating-Current to Direct-Current
ADC	Analog-to-Digital Converter
BCM	Boundary Conduction Mode
BiCMOS	Bipolar Complementary Metal-Oxide Semiconductor
BJT	Bipolar Junction Transistor
BW	BandWidth
CB	Conduction Boundary
CFL	Compact Fluorescent Lamps
CM	Conduction Mode
CCM	Continuous Conduction Mode
CMOS	Complementary Metal-Oxide Semiconductor
COOT	Constant On/Off-Time
CRT	Cathode Ray Tube
DAC	Digital-to-Analog Converter
DC	Direct-Current
DC-AC	Direct-Current to Alternating-Current
DC-DC	Direct-Current to Direct-Current
DCM	Discontinuous Conduction Mode
DIL	Dual In Line
EEF	Efficiency Enhancement Factor
EMI	Electro Magnetic Interference
FAIMS	High-Field Asymmetric waveform Ion Mobility Spectrometry
FET	Field-Effect Transistor
ESI	Electro-Spray Ionization
ESL	Electric Series inductance
ESR	Electric Series Resistance
FOX	Field Oxide
F <sup>2</sup> SCOOT	Feed-Forward Semi-Constant On/Off-Time

GBW	Gain BandWidth
GND	GrouND
HF	High Frequency
IC	Integrated Circuit
IGBT	Insulated Gate Bipolar Transistor
LDO	Low Drop-Out
LIDAR	Laser Imaging Detection And Ranging
LiION	Lithium-ION
ME1	Metal-1
MIM	Metal-Insulator-Metal
MOM	Metal-Oxide-Metal
MOS	Metal-Oxide Semiconductor
MOSFET	Metal-Oxide Semiconductor Field-Effect Transistor
n-MOSFET	n-channel Metal-Oxide Semiconductor Field-Effect Transistor
MS	Mass Spectrometry
MUX	Multi-PleXer
NPN	<i>n</i> -type <i>p</i> -type <i>n</i> -type transition
OPAMP	OPerational AMPLifier
OTA	Operational Transconductance Amplifier
OX1	Oxide-1
PC	Personal Computer
PCB	Printed Circuit Board
PFC	Power Factor Correction
PFM	Pulse Frequency Modulation
p-MOSFET	p-channel Metal-Oxide Semiconductor Field-Effect Transistor
PNP	<i>p</i> -type <i>n</i> -type <i>p</i> -type transition
PSRR	Power Supply Rejection Ratio
PTC	Positive temperature coefficient
PWM	Pulse Width Modulation
Q.E.D.	Quod Erat Demonstrandum
RC	Resistor-Capacitor
RF	Radio-Frequency
RL	Resistor-Inductor
RLC	Resistor-Inductor-Capacitor
RMS	Root-Mean-Square
SCOOT	Semi-Constant On/Off-Time
SEPIC	Single-Ended Primary-Inductance Converter
SiGe	Silicon-Germanium
SIMO	Single-Inductor Multiple-Output
SMOC	Series Multiple-Output Converter
SMOS	Type of healthy sandwich
SMPS	Switched-Mode Power Supply
SoC	System-on-Chip
SPICE	Simulation Program with Integrated Circuit Emphasis

SRR	Supply Rejection Ratio
SW	Switch

*Symbols and Quantities*

$A$	Area
$A_C$	On-chip capacitor area
$A_C^+$	Positive charge balance area
$A_C^-$	Negative charge balance area
$A_L$	Perpendicular projected area of the inductor windings
$A_L^+$	Positive volt-second balance area
$A_L^-$	Negative volt-second balance area
arccos	Arc cosine
$A_\varnothing$	Perpendicular cross-sectional area
$A_{\varnothing\_eff}$	Effective $A_\varnothing$
$C$	Capacitance
$C_{eq}$	Equivalent capacitance
cos	Cosine
$C_{db}$	Parasitic drain-bulk capacitance
$C_{dec}$	Input decouple capacitance
$C_{gb}$	Parasitic gate-bulk capacitance
$C_{gd}$	Parasitic gate-drain capacitance
$C_{gc}$	Parasitic gate-source capacitance
$C_{gg}$	Parasitic gate capacitance
$C_{g\_min}$	Parasitic gate of a minimal size inverter
$C_{sb}$	Parasitic source-bulk capacitance
$C_{in}$	Input capacitance
$C_{out}$	Output capacitance
$C_{tot}$	Total capacitance
$C_{out\_tot}$	Total output capacitance
$C_{out\_1}$	Capacitance of output 1
$C_{pad}$	Parasitic substrate capacitance of a bonding pad
$C_{par}$	Parasitic capacitance
$C_{sub}$	Parasitic substrate winding capacitance
$C_1$	Capacitance 1
$d$	Thickness
$d$	Pitch between two conductors
$d_{ox}$	Thickness of the oxide
$e$	Euler's constant: 2.718281828...
$E_{C\_in}$	Energy stored in $C$
$E_{C\_out}$	Energy delivered by $C$
$E_C(t)$	Energy stored in $C$ as a function of $t$
$E_{C_1}$	Energy stored in $C_1$
$E_{C_2}$	Energy stored in $C_2$
$E_{C_1C_2}$	Energy stored in $C_1$ and $C_2$
$E_{C_1 \rightarrow C_2}$	Transferred energy from $C_1$ to $C_2$
$E_{C_1 \rightarrow R}$	Transferred energy from $C_1$ to $R$

$E_{C_1 \rightarrow RC}$	Transferred energy from $C_1$ to $RC$
$EEF$	Efficiency Enhancement Factor
$\overline{EEF}$	Mean Efficiency Enhancement Factor
$\widetilde{EEF}$	Weighted Efficiency Enhancement Factor
$EEF(P_{out\_i})$	$EEF$ as a function of the $i$ th $P_{out}$
$E_L$	Magnetic energy stored in $L$
$E_{L\_in}$	Energy stored in $L$
$E_{L\_out}$	Energy delivered by $L$
$E_L(t)$	Magnetic energy stored in $L$ as a function of $t$
$E_L(t)$	Energy stored in $L$ as a function of $t$
$E_R(t)$	Energy dissipated in $R$ as a function of $t$
$E_{R_2}$	Energy dissipated in $R_2$ in steady-state
$E_{R_2}(t)$	Energy dissipated in $R_2$ as a function of $t$
$E_{U_{in}}(t)$	Energy delivered by $U_{in}$ as a function of $t$
$E_{U_{in} \rightarrow C_1}$	Transferred energy from $U_{in}$ to $C_1$
$E_{U_{in} \rightarrow C_1 C_2}$	Transferred energy from $U_{in}$ to $C_1$ and $C_2$
$E_{U_{in} C_1 \rightarrow C_2}$	Transferred energy from $U_{in}$ and $C_1$ to $C_2$
$E_{U_{in} \rightarrow C}(t)$	Transferred energy from $U_{in}$ to $C$ as a function of $t$
$E_{U_{in} \rightarrow L}(t)$	Transferred energy from $U_{in}$ to $L$ as a function of $t$
$E_{U_{in} \rightarrow R}(t)$	Transferred energy from $U_{in}$ to $R$ as a function of $t$
$E_{U_{in} \rightarrow RC}(t)$	Transferred energy from $U_{in}$ to $R$ and $C$ as a function of $t$
$E_{U_{in} \rightarrow RL}(t)$	Transferred energy from $U_{in}$ to $R$ and $L$ as a function of $t$
$E_{U_{in} \rightarrow RLC}(t)$	Transferred energy from $U_{in}$ to $R$ , $L$ and $C$ as a function of $t$
$f$	Frequency
$F$	Global effective fan-out
$f_{scale}$	Scaling factor
$f_{SW}$	Switching frequency
$f_0$	Resonance frequency
$g_1\{\}$	Function $g_1$
$H(f_{SW})$	Transfer function as a function of $f_{SW}$
$I$	Current
$I_{ak}$	Anode-cathode current
$I_b$	Base current
$I_c$	Collector current
$i_{C\_charge}$	Charge current through $C$
$i_{C\_discharge}$	Discharge current through $C$
$I_{C\_leak}$	Leakage current through $C$
$I_{cs}$	Control system supply current
$i_C(t)$	Current through $C$ as a function of $t$
$i_{C1}$	Current 1 through $C$
$i_{C2}$	Current 2 through $C$
$I_{ds}$	Drain-source current
$I_e$	Emitter current
$I_{in}$	Input current
$I'_{in\_max}$	Maximum input current

$I'_{in\_min}$	Minimum input current
$I_{in\_RMS}$	RMS input current
$I_L$	Mean current through $L$
$I_{L\_max}$	Maximal current through $L$
$I_{L\_min}$	Minimal current through $L$
$i_L(t)$	Current through $L$ as a function of $t$
$i_L(0)$	Initial current through $L$
$I_{out}$	Output current
$I_{out}$	Mean output current
$I_{out\_RMS}$	RMS output current
$I_{out}(t)$	Output current as a function of $t$
$i_{prim}$	Current through primary winding
$i_{prim}(s)$	Current through primary winding, in the Laplace-domain
$i_{Rb}(t)$	Current through $R_b$ as a function of $t$
$i_{Rc}(t)$	Current through $R_c$ as a function of $t$
$i_{sec}$	Current through secondary winding
$i_{sec}(s)$	Current through secondary winding, in the Laplace-domain
$i_{SW}$	Current through $SW$
$I_{SW1\_RMS}$	RMS current through $SW1$
$i_{SW2}$	Mean current through $SW2$
$i_{SW2}(t)$	Current through $SW2$ as a function of $t$
$i(t)$	Current as a function of $t$
$k$	Voltage conversion ratio
$K$	Form-factor fitting parameter
$k(f_{SW})$	Voltage conversion ratio as a function of $f_{SW}$
$k_{lin}$	Voltage conversion ratio of a linear voltage converter
$k_{lin\_max}$	Maximal voltage conversion ratio of a linear voltage converter
$k_M$	Magnetic coupling factor
$k_{SW}$	Voltage conversion ratio of a switched-mode voltage converter
$k(\delta)$	Voltage conversion ratio as a function of $\delta$
$\ell$	Length of a conductor
$L$	Inductance
$L_{Cs}$	Parasitic series inductance of $C$
lim	Limit
$L_{line}$	Metal line length
$L_M$	Magnetizing inductance
ln	Natural logarithm
$L_n$	Gate-length of an nMOSFET
$L_{p\_buff}$	$L_p$ of a buffer
$\ell_{overlap}$	Overlapping length of two conductors
$L_p$	Gate-length of an pMOSFET
$L_{prim}$	Primary winding inductance
$L_{sec}$	Secondary winding inductance
$L_{self}$	Self inductance
$L_{tot}$	Total inductance



$L_{track}$	Length of a metal track
$L_1$	Inductance 1
$\mathcal{L}^{-1}$	Inverse Laplace-transform
$M$	Mutual inductance
$M^+$	Positive mutual inductance
$M^-$	Negative mutual inductance
$n$	Number of stages/phases
$N_a$	Doping concentration
$n_{prim}$	Number of turns in the primary winding
$n_{sec}$	Number of turns in the secondary winding
$n_{Tr}$	Winding turn ratio
$n_1$	Number of turns of winding 1
$P_{buff\_cpar}$	Power loss in parasitic capacitances in buffers
$P_{buff\_short}$	Power loss due to short-circuit current in buffers
$P_C$	Power for charging a capacitor
$P_{Df}$	Diode forward conduction power loss
$P_{diss}$	Dissipated power
$P_{in}$	Input power
$P_{in\_lin}$	Input power of a linear DC-DC voltage converter
$P_{in\_SW}$	Input power of switched-mode DC-DC voltage converter
$P_{L\_Csub}$	Parasitic substrate capacitance power loss of an inductor
$P_{out}$	Output power
$P'_{out}$	Real output power
$P_{out\_lin}$	Output power of a linear DC-DC voltage converter
$P_{out\_max}$	Maximal output power
$P_{out\_SW}$	Output power of a switched-mode DC-DC voltage converter
$P_{Rcs}$	Parasitic series resistance power loss
$P_{Rcp}$	Parasitic parallel resistance power loss
$P_{Rin}$	Power loss in $R_{in}$
$P_{Ron}$	Power loss in $R_{on}$
$P_{Rout}$	Power loss in $R_{out}$
$P_{Rsw1}$	Power loss in $R_{sw1}$
$P_{tf\_SW1}$	Fall-time power loss of SW1
$P_{tr\_SW1}$	Rise-time power loss of SW1
$Q$	Q-factor
$Q_d$	Charge in the drain
$Q_g$	Charge in the gate
$Q_s$	Charge in the source
$Q_{in}$	Stored charge
$Q_{out}$	Delivered charge
$r$	Perpendicular cross-section radius a round conductor
$R$	Resistance
$R_a$	Equivalent resistance
$R_b$	Equivalent resistance
$R_{bondwire}$	Parasitic series resistance of a bondwire

$R_c$	Equivalent resistance
$R_{channel\Box}$	Square-resistance of the induced channel
$R_{Cdec}$	Parasitic series resistance of $C_{dec}$
$R_{cont\_f}$	Parasitic series resistance of gate contacts
$R_{cont\_ds}$	Parasitic series resistance of drain/source contacts
$R_{Cp}$	Parasitic parallel resistance of $C$
$R_{Cs}$	Parasitic series resistance of $C$
$R_e$	Equivalent load resistance
$R_{eq}$	Equivalent resistance
$R_{in}$	Input resistance
$R_{in}$	Parasitic series resistance of $U_{in}$
$R_L$	Load resistance
$R'_L$	Real load resistance
$R_{left}$	Conductor series resistance, seen from the left
$R_{Ls}$	Parasitic series resistance of $L$
$R_{Ls@T}$	$R_{Ls}$ at temperature $T$
$R_{Ls@T+\Delta T}$	$R_{Ls}$ at temperature $T + \Delta T$
$R_{line}$	Line resistance
$R_{loss}$	Additional loss resistance
$R_{n+\Box}$	Square-resistance of $n^+$ -region
$R_{on}$	On-resistance
$R_{on@T}$	$R_{on}$ at temperature $T$
$R_{on@T+\Delta T}$	$R_{on}$ at temperature $T + \Delta T$
$R_{on\_n}$	On-resistance of an n-MOSFET
$R_{on\_p}$	On-resistance of an p-MOSFET
$R_{out}$	Parasitic output resistance
$R_{poly\Box}$	Square-resistance of poly-silicon
$R_{right}$	Conductor series resistance, seen from the right
$R_{sen}$	Sense resistance
$R_{series}$	Variable series resistance of a series voltage converter
$R_{shunt}$	Variable shunt resistance of a shunt voltage converter
$R_{SW1}$	Parasitic series resistance of $SW_1$
$R_{track}$	Parasitic series resistance of a metal track
$R_{via}$	Parasitic via series resistance
$R_{via\_tot}$	Total parasitic via series resistance
$R_0$	Output resistance at $f_0$
$R\Box$	Square-resistance
$s$	Laplace-transform operator
$\sin$	Sine
$t$	Time
$T$	Period
$T$	Temperature
$t_{a\rightarrow b}$	Time from point $a$ to point $b$
$t_{a\rightarrow c}$	Time from point $a$ to point $c$
$t_{b\rightarrow c}$	Time from point $b$ to point $c$

$t_d$	Dead-time
$t_f$	Fall-time
$t_{f\_SW1}$	Fall-time $SW_1$
$t_{flank}$	Mean rise/fall-time
$t_{on}$	On-time
$t_{off}$	Off-time
$t_{off\_real}$	Real off-time
$t_{ox}$	MOSFET gate-oxide thickness
$t_r$	Rise-time
$t_{r/f}$	Rise/fall-time
$t_{r\_SW1}$	Rise-time $SW_1$
$Tr$	Transformer
$t_{SW}$	Switching/Charging time
$t_{zerol}$	Intersect time 1 with the X-axis
$t_1$	Time 1
$U$	Voltage
$U_{be}$	Base-emitter voltage
$U_{ce}$	Collector-emitter voltage
$U_{C\_max}$	Maximal voltage over $C$
$U_{C\_min}$	Minimal voltage over $C$
$u_C(t)$	Voltage over $C$ as a function of $t$
$U_C(T)$	Voltage over $C$ at the end of $T$
$U_C(0)$	Initial voltage over $C$
$U_{dd}$	Nominal technology supply voltage
$U_{Df}$	Diode forward voltage drop
$U_{ds}$	Drain-source voltage
$U_{dsatp}$	Drain-source saturation voltage of a p-MOSFET
$U_{dsn}$	Drain-source voltage of an n-MOSFET
$U_{err}$	Error-voltage
$U_{gb}$	Gate-bulk voltage
$U_{g\_od}$	Gate-overdrive voltage
$U_{gs}$	Gate-source voltage
$U_{gsn}$	Gate-source voltage of an n-MOSFET
$U_{in}$	Input voltage
$U'_{in\_max}$	Maximum input voltage
$U'_{in\_min}$	Minimum input voltage
$U_{in\_peak}$	Peak value of $U_{in}$
$u_L(t)$	Voltage over $L$ as a function of $t$
$U_{L1}$	Voltage 1 over $L$
$U_{offset}$	Offset voltage
$U_{out}$	Output voltage
$\overline{U_{out}}$	Mean output voltage
$U_{out\_max}$	Maximal output voltage
$U_{out\_min}$	Minimal output voltage
$U_{out\_RMS}$	RMS output voltage

$U'_{out\_RMS}$	Real RMS output voltage
$u_{out}(t)$	Output voltage as a function of $t$
$u_{out}(x)$	Output voltage as a function of $x$
$\hat{u}_{out}(x)$	Output voltage amplitude as a function of $x$
$\hat{u}_{out}(\theta)$	Output voltage amplitude as a function of $\theta$
$U_{prim}$	Voltage over the primary winding
$U_{out\_ptp}$	Peak-to-peak output voltage
$u_{Ra}(t)$	Voltage over $R_a$ as a function of $t$
$u_{Rb}(t)$	Voltage over $R_b$ as a function of $t$
$u_{Rc}(t)$	Voltage over $R_c$ as a function of $t$
$u_{RCp}(t)$	Voltage over $R_{Cp}$ as a function of $t$
$u_{RCs}(t)$	Voltage over $R_{Cs}$ as a function of $t$
$U_{ref}$	Reference voltage
$u_R(t)$	Voltage over $R$ as a function of $t$
$U_{sb}$	Source-bulk voltage
$U_{sen}$	Sense voltage
$U_{sec}$	Voltage over the secondary winding
$u_{SW}$	Voltage over $SW$
$U_{SW_3}$	Voltage over $SW_3$
$U_{tria}$	Triangular waveform voltage
$V_t$	Threshold voltage
$W_{drain}$	Drain-width
$W_n$	Gate-width of an nMOSFET
$W_p$	Gate-width of an pMOSFET
$W_{p\_buff}$	$W_p$ of a buffer
$W_{source}$	Source-width
$W_{track}$	Width of a metal track
$x$	$\Delta U_{out}$ approximation variable
$Z_{in}$	Input impedance
$Z_k$	Impedance ratio
$Z_{out}$	Output impedance
$Z_1$	Impedance 1
$\alpha$	Resistance temperature coefficient
$\alpha(P_{out})$	Power activity probability distribution
$\delta$	Duty-cycle
$\delta_{skin}$	Skin-depth
$\Delta I_{in}$	Input current ripple
$\Delta I_L$	Current ripple through $L$
$\Delta I_{L\_tot}$	Total current ripple through $L$
$\Delta I_{L\_1}$	Current ripple through $L_1$
$\Delta P_{in}$	Input power difference
$\Delta T$	Temperature difference
$\Delta U$	Voltage difference
$\Delta U_C$	Voltage swing over a capacitor
$\Delta U_{in}$	Input voltage ripple

$\Delta U_L$	Voltage swing over an inductor
$\Delta U_{out}$	Output voltage ripple
$\Delta U_{out}(\delta)$	Output voltage ripple as a function of $\delta$
$\Delta Q$	Charge difference
$\Delta Q_{SW}$	Transferred charge in one switch cycle
$\Delta \eta$	Power conversion efficiency difference
$\epsilon$	Dielectric permittivity
$\epsilon_0$	Permittivity of vacuum
$\epsilon_{r\_ox}$	Relative permittivity of an oxide
$\eta$	Power conversion efficiency
$\eta_{C\_charge}$	Energy charging efficiency of $C$
$\eta_{C\_charge}(t)$	$\eta_{C\_charge}$ as a function of $t$
$\eta_{L\_charge}$	Energy charging efficiency of $L$
$\eta_{L\_charge}(t)$	$\eta_{L\_charge}$ as a function of $t$
$\eta_{RLC\_charge}(t)$	$\eta_{C\_charge}$ in an $RLC$ -circuit as a function of $t$
$\eta_{lin}$	Power conversion efficiency of a linear DC-DC voltage converter
$\eta_{sp\_down}$	Power conversion efficiency of a step-down charge-pump
$\eta_{sp\_up}$	Power conversion efficiency of a step-up charge-pump
$\eta_{SW}$	Power conversion efficiency of a switched-mode DC-DC converter
$\eta_{SW\_max}$	Maximal $\eta_{SW}$
$\eta_{Tr}$	Power conversion efficiency of an ideal transformer
$\eta_{Tr}(t)$	$\eta_{Tr}$ as a function of $t$
$\eta_{\Phi_1}$	Energy conversion efficiency of $\Phi_1$
$\gamma$	Thermal resistance
$\Phi_1$	Phase 1
$\kappa$	CMOS technology scaling factor
$\lambda_p$	Early voltage of a p-MOSFET
$\mu_n$	n-carrier mobility
$\mu_p$	p-carrier mobility
$\mu$	Magnetic Permeability
$\mu_r$	Relative permeability
$\pi$	Circumference/diameter ratio of a circle: 3.141592654...
$\rho$	Resistivity
$\tau_C$	Time constant of an $RC$ -circuit
$\tau_L$	Time constant of an $RL$ -circuit
$\tau_{LC}$	Time constant of an $RLC$ -circuit
$\tau_{Tr}$	Time constant of the primary winding of a transformer
$\theta$	Phase difference
$\omega_{LC}$	Angular frequency of an $RLC$ -circuit
$\Upsilon$	$\Delta U_{out}$ approximation function
$\#fingers$	Number of gate fingers of a MOS capacitor
$\#C_{out\_1}$	Total required $C$ to implement $C_{out\_1}$
$\#C_{out\_tot}$	Total required $C$ to implement $C_{out\_tot}$
$\#seg$	Number of segments
$\#via$	Number of vias

$\infty$	Infinite
■	Q.E.D.
✓	A benefit
✗	A drawback

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